

# XPS analysis of pyrite thin films

*Ming H. Cheng*

John C. Hemminger group

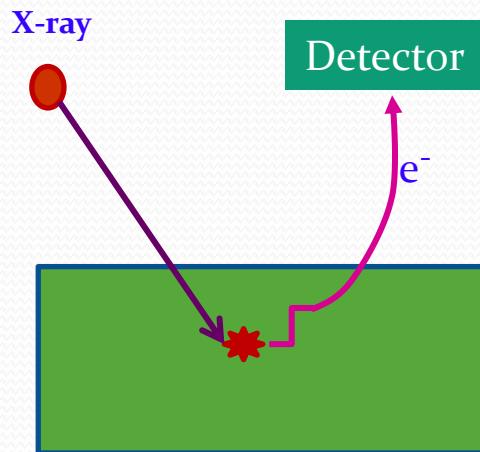
August 3, 2010

# Outline

- **Introduction of XPS**
- **Pyrite thin films on the glass**
  - Na migration to the surface
  - Ar sputtering effect
- **Pyrite thin films on the quartz**
  - Removal of oxidation layers on the surface
  - Time-dependent oxidation study
- **Pyrite thin films on the Si substrate**
  - Synchrotron radiation (Advance Light Source in Berkeley National Labs)
  - Surface chemical states of pyrite thin films on the Si substrate

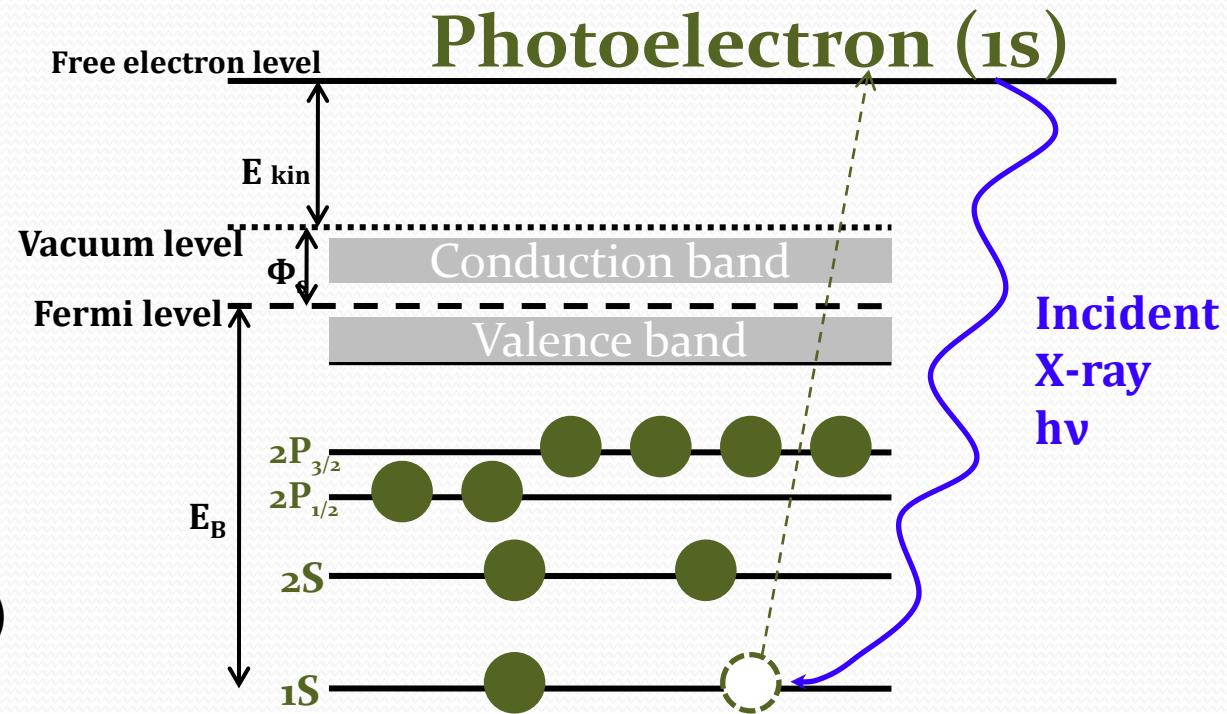
# The principle of X-ray photoelectron spectroscopy (XPS)

## Photoelectron effect



Ultra-high vacuum ( $<10^{-9}$  torr)  
is required.

## XPS energy level diagram

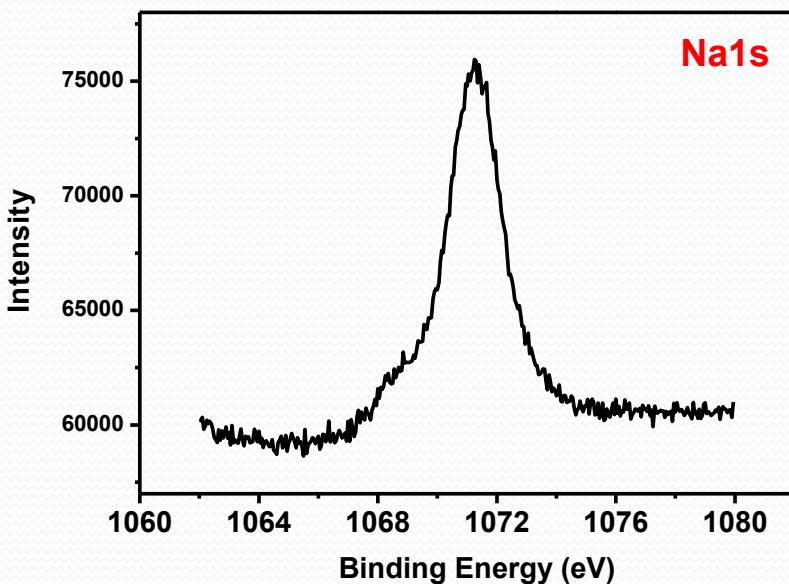
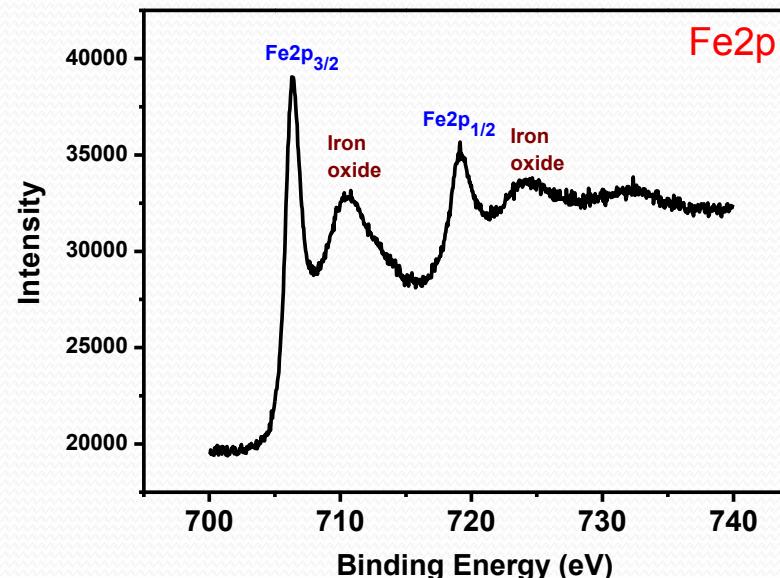
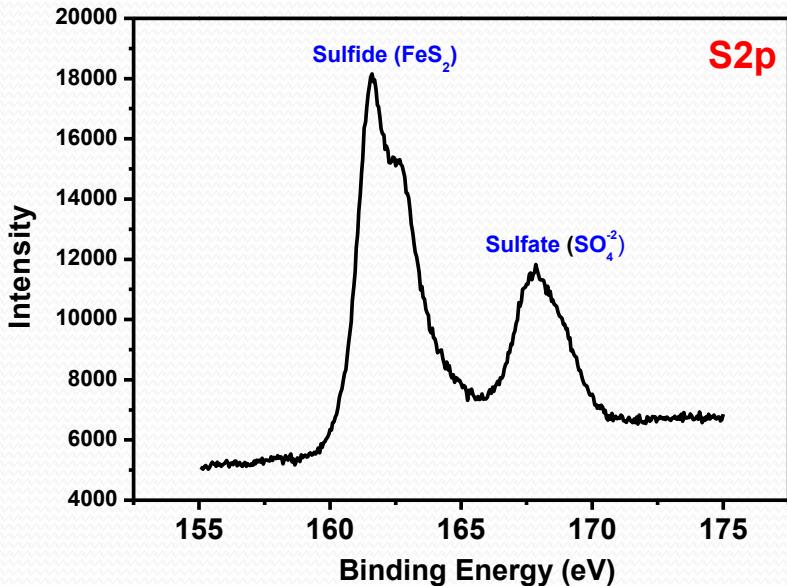


$$E_{kin} = h\nu - E_B - \Phi_s$$

$E_{kin}$  : The kinetic energy of ejected photoelectrons;  $E_B$  : Binding Energy

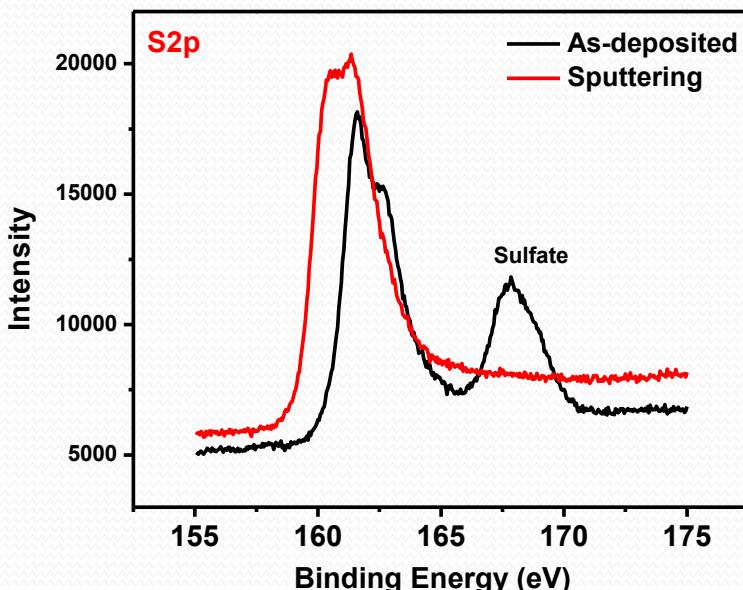
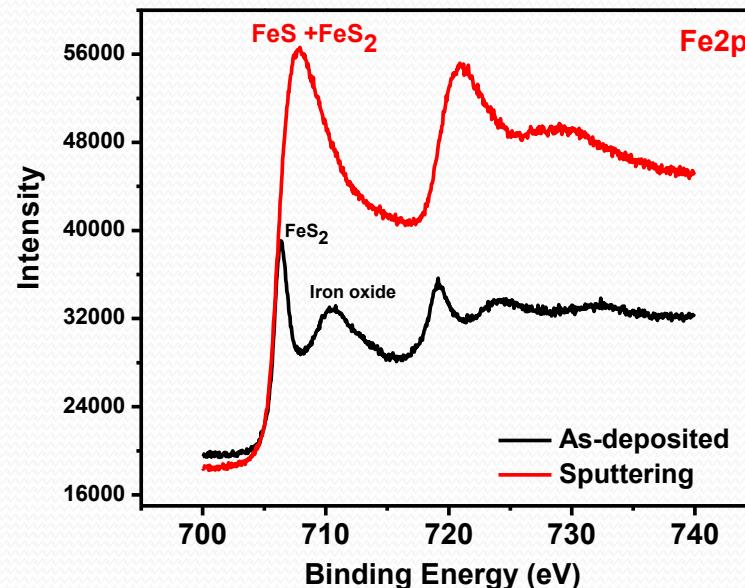
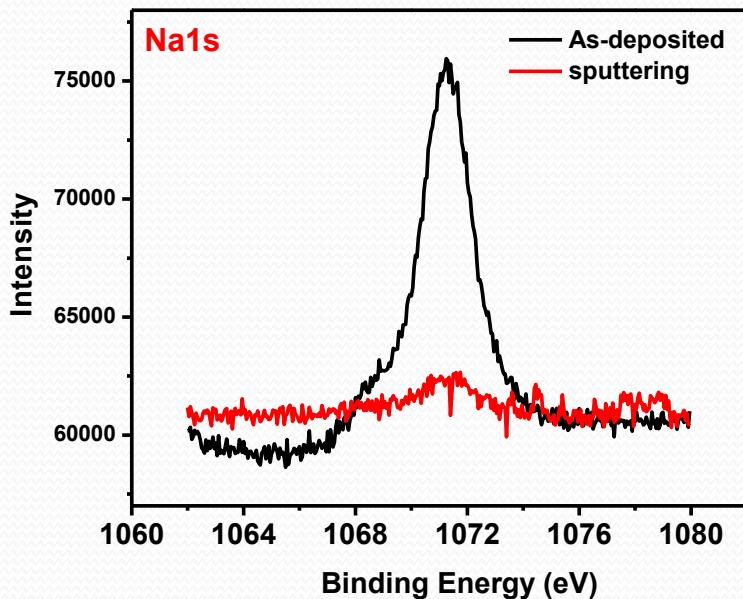
$h\nu$  : The energy of the incident X-ray photons.  $\Phi_s$  : Work function term (almost constant)

# Pyrite thin films on the glass



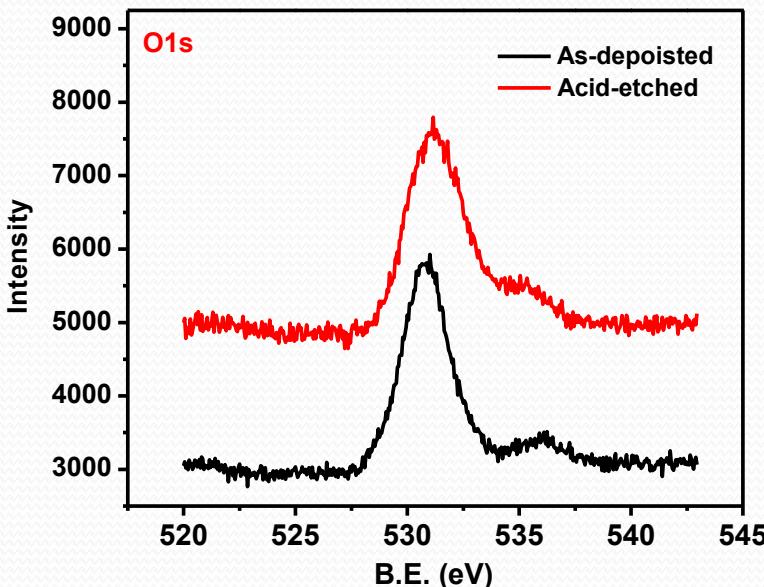
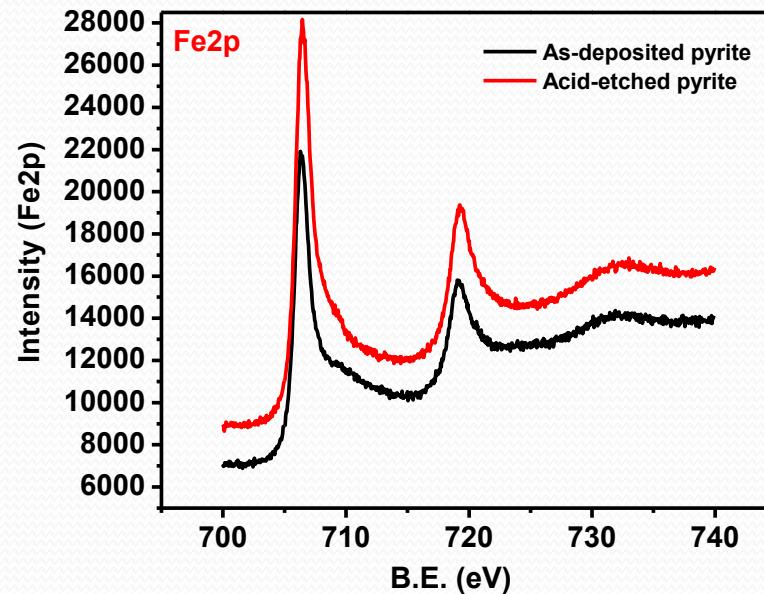
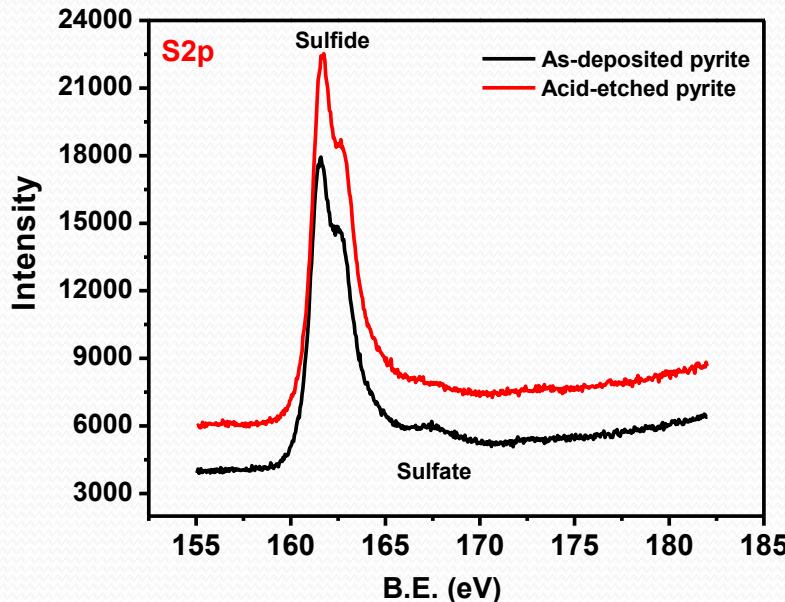
- The pyrite has been **oxidized**.
- **Na exists** on the surface of the pyrite thin film.

# As-deposited VS Sputtered



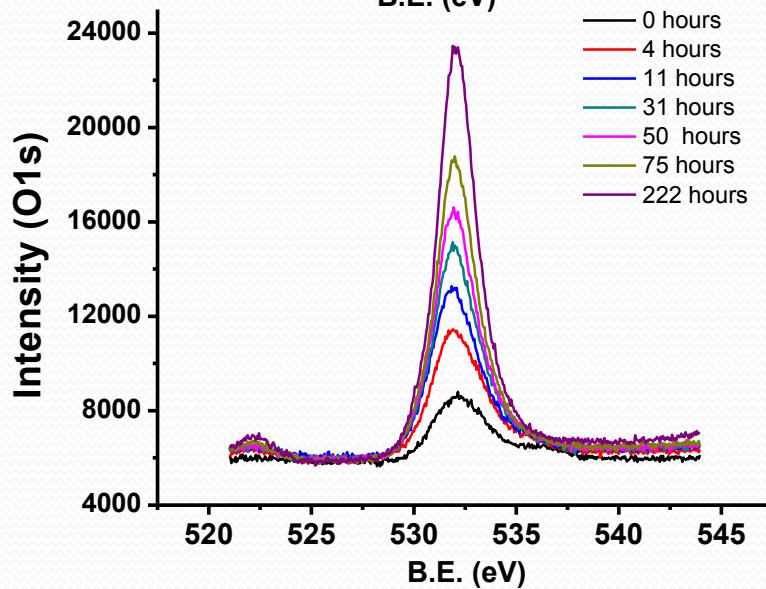
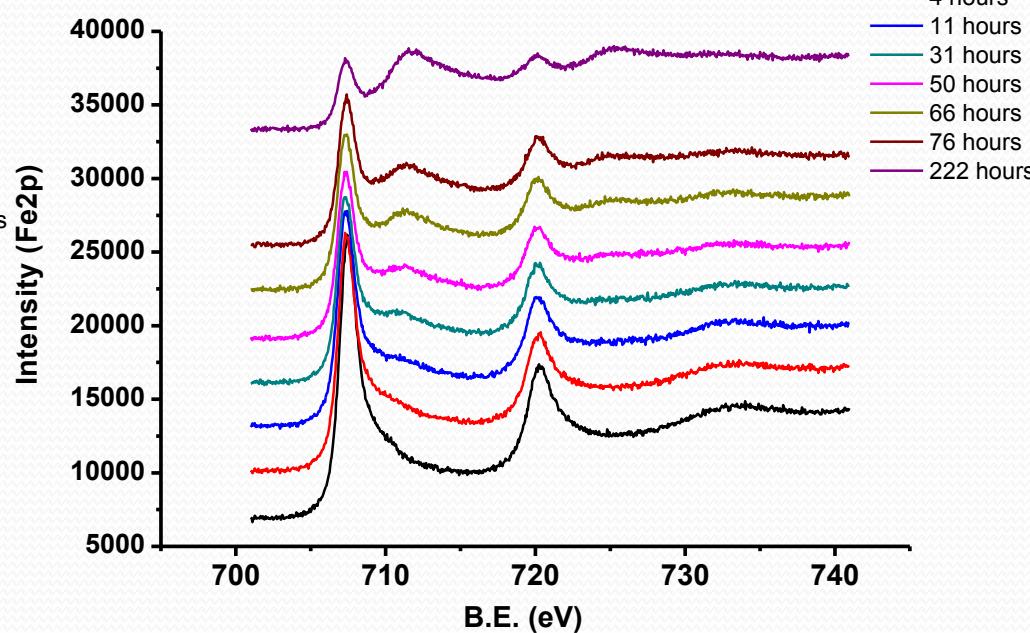
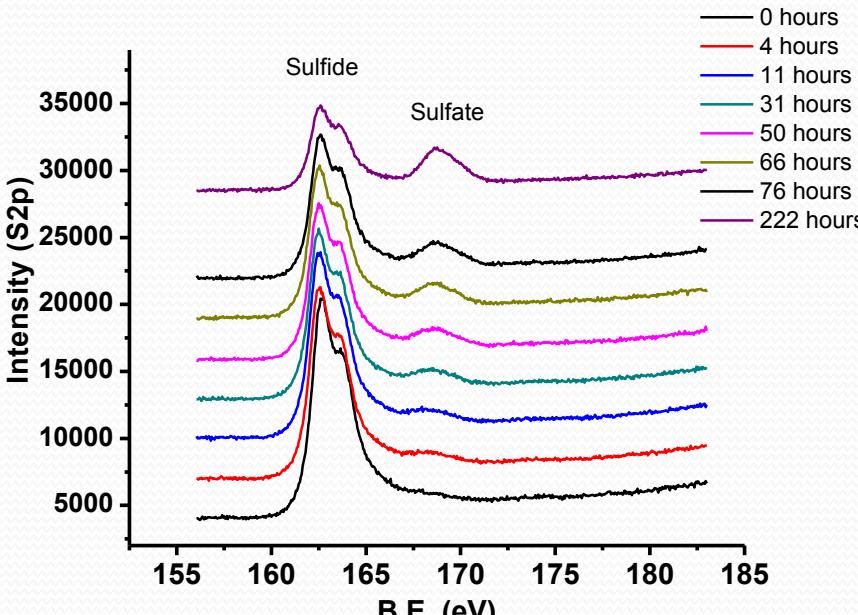
- **Sputtering condition:** 5\*10<sup>-5</sup> torr Ar, 2 KV (beam energy), 20mA (emission current), 5 mins.
- **Na is removed** by Ar sputtering which indicates Na only exists on the surface.
- The broadening of Fe 2p and S2p peaks after Ar sputtering is attributed to **sulfur preferential sputtering**.

# Pyrite thin films on the quartz



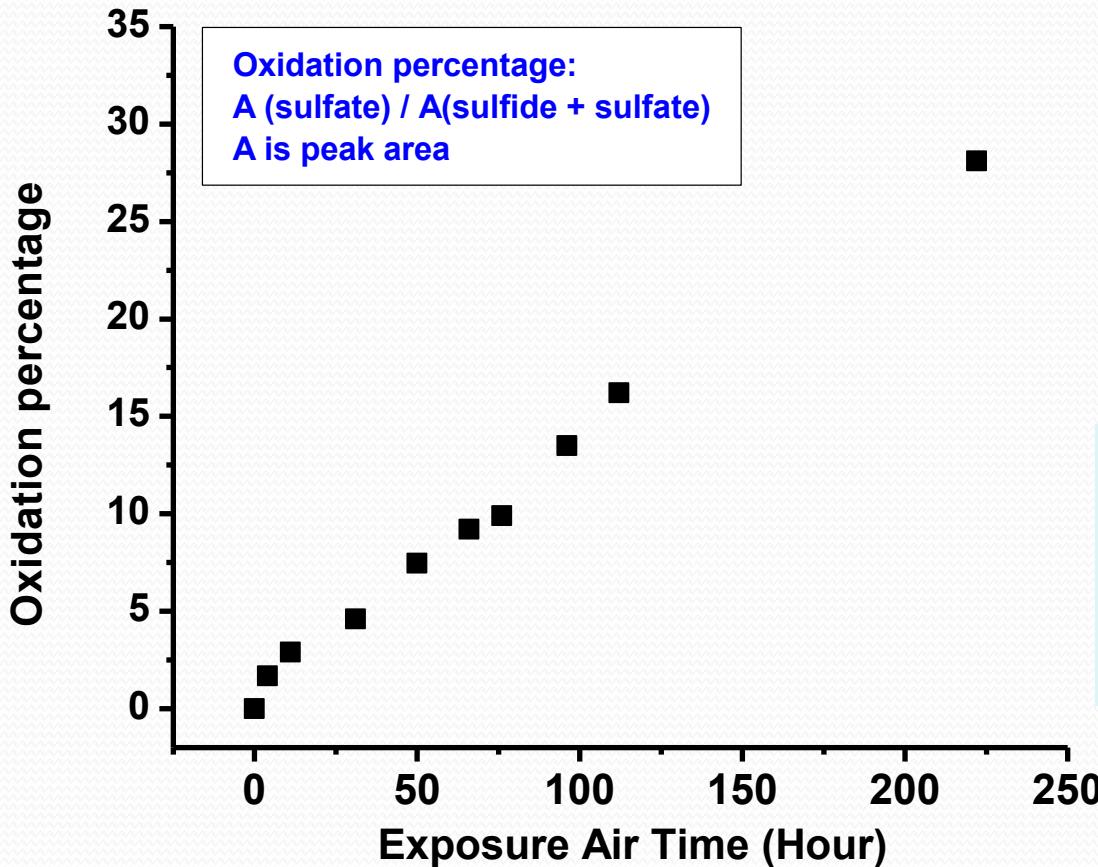
- The composition of mixed acid used for removing the oxide layer is:  
**0.1% HF, 0.1% Acetic acid, and 0.1% Nitric acid**
- The oxide layer can be removed by this mixed acid.

# Time-dependent oxidation study of acid-etched pyrite thin films on the quartz



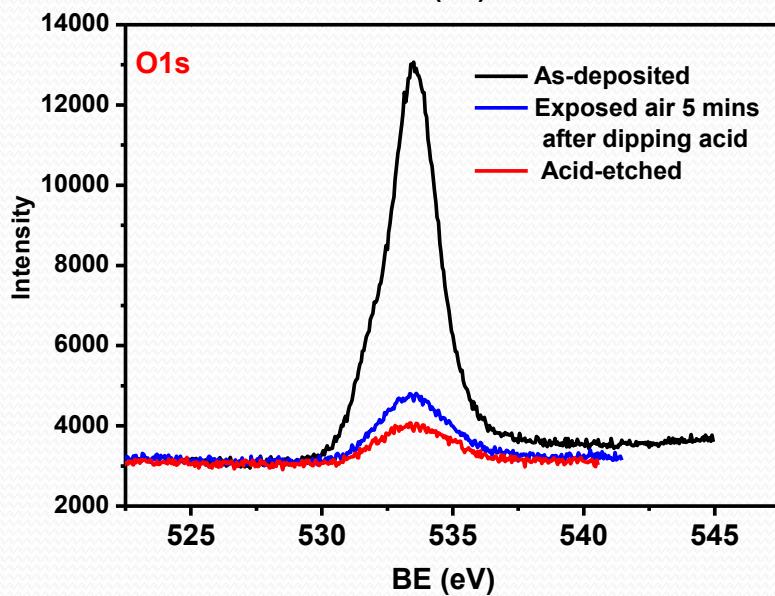
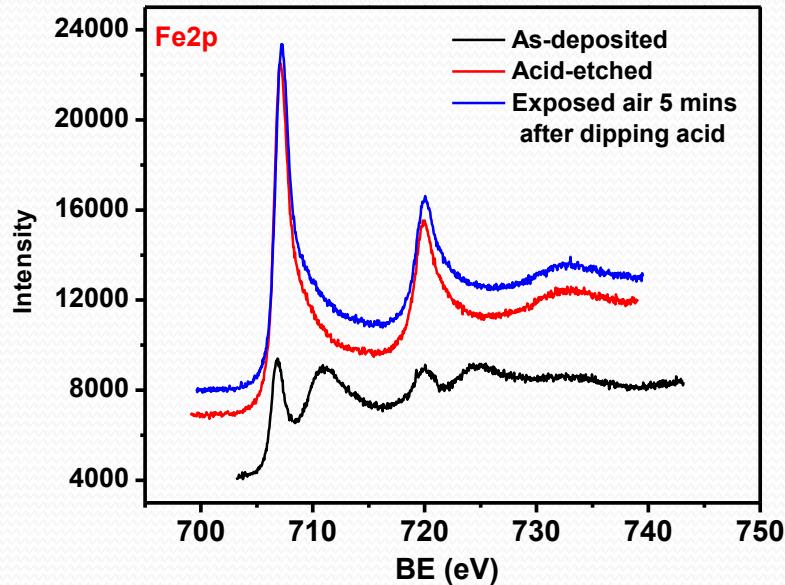
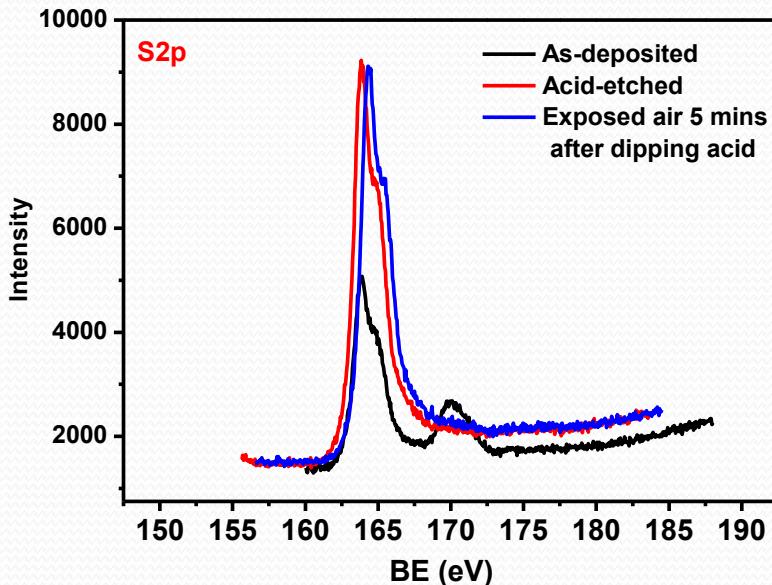
- The oxide layer grows with respect to exposure air time.

# Time-dependent oxidation study of acid-etched pyrite thin films on quartz



• This oxidation study is still **in progress**, since the oxide layer is **NOT saturated**.

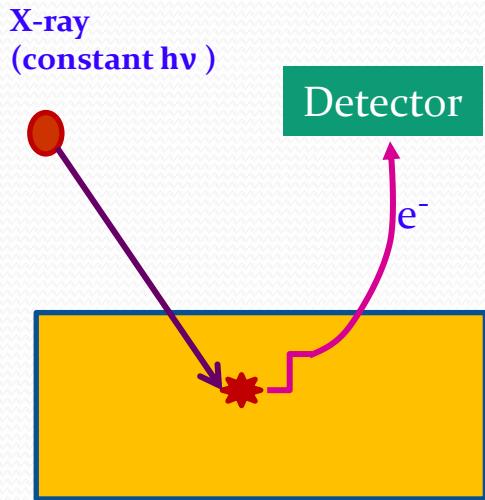
# Pyrite thin films on the Si (in Irvine)



- After dipping the acid solution, the oxide layer was removed.
- The acid-etched pyrite keeps unoxidized after exposing to air 5 mins.

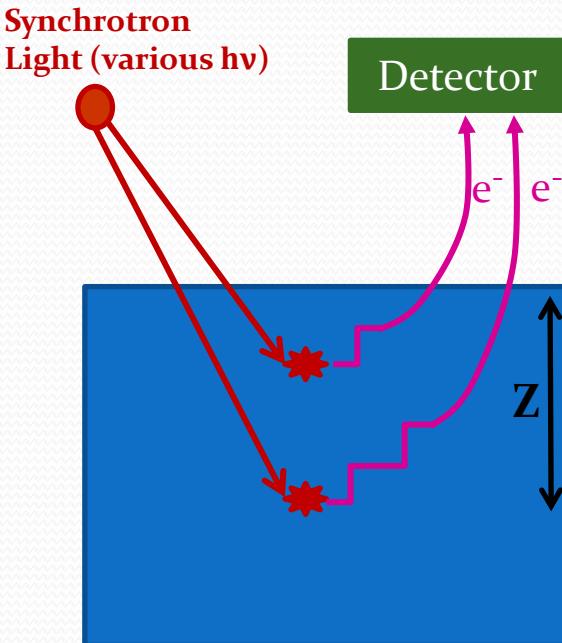
# Depth profile experiment and inelastic mean free path (IMFP)

## Photoelectron effect

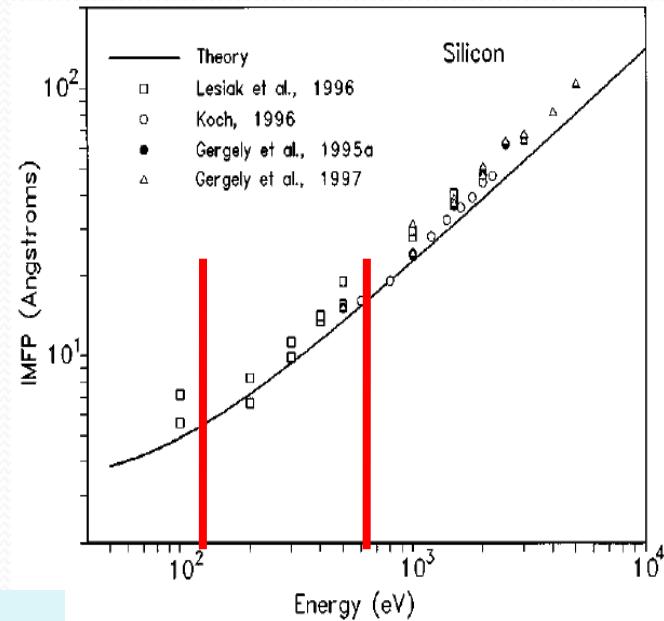


$$E_{\text{kin}} = h\nu - E_B - \Phi_s$$

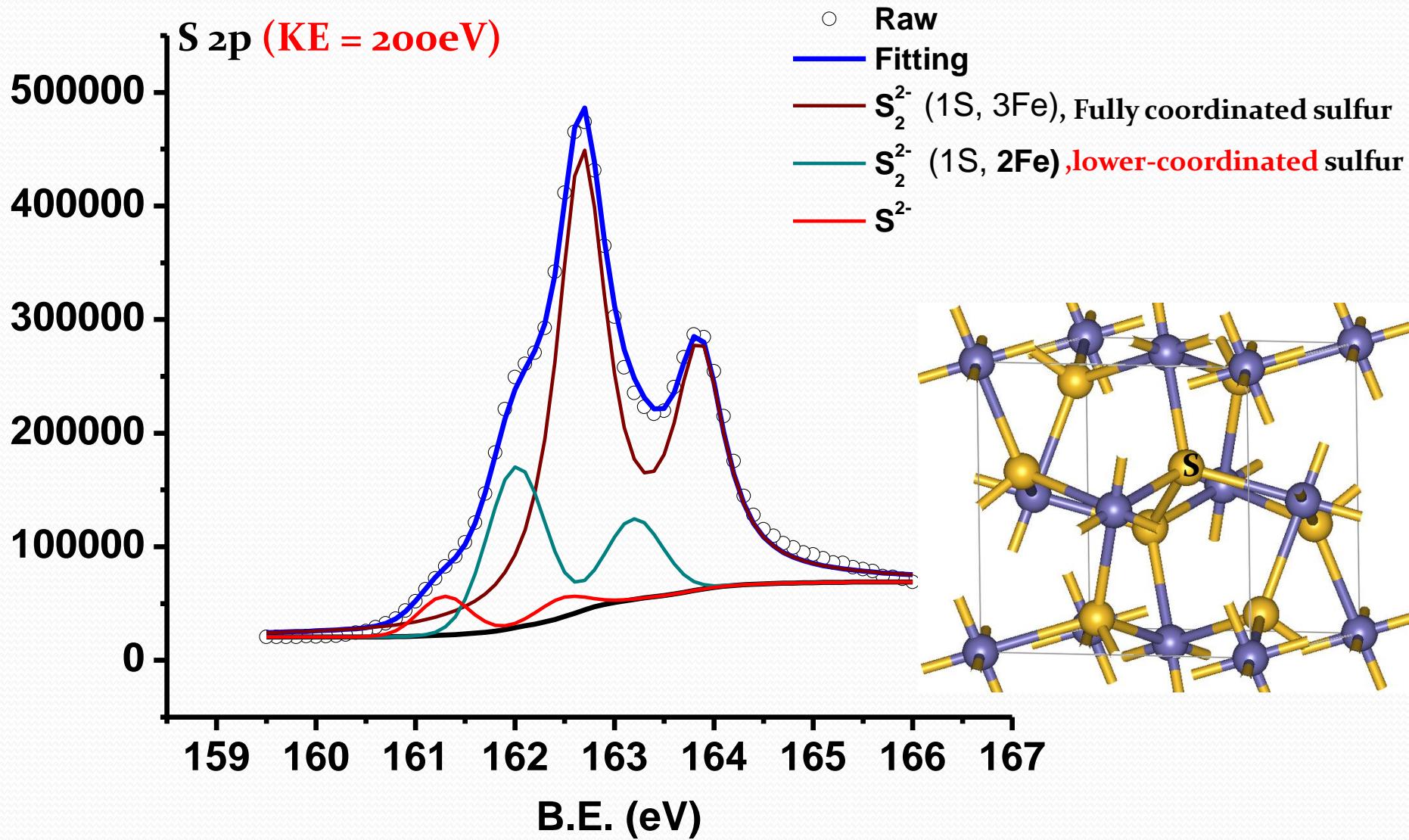
## Depth profile experiment



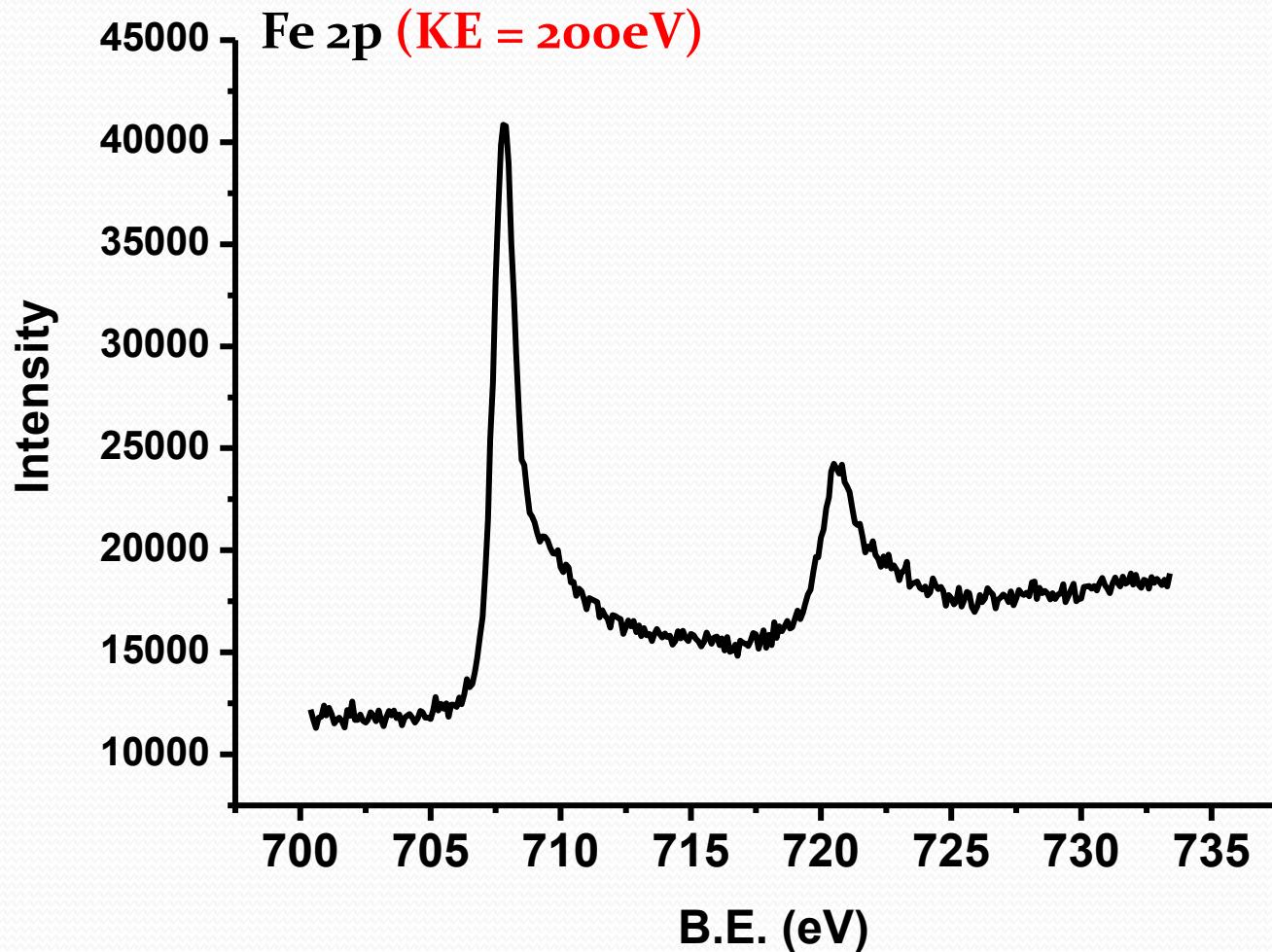
Photoelectrons with different kinetic energies come from different depth of the sample.



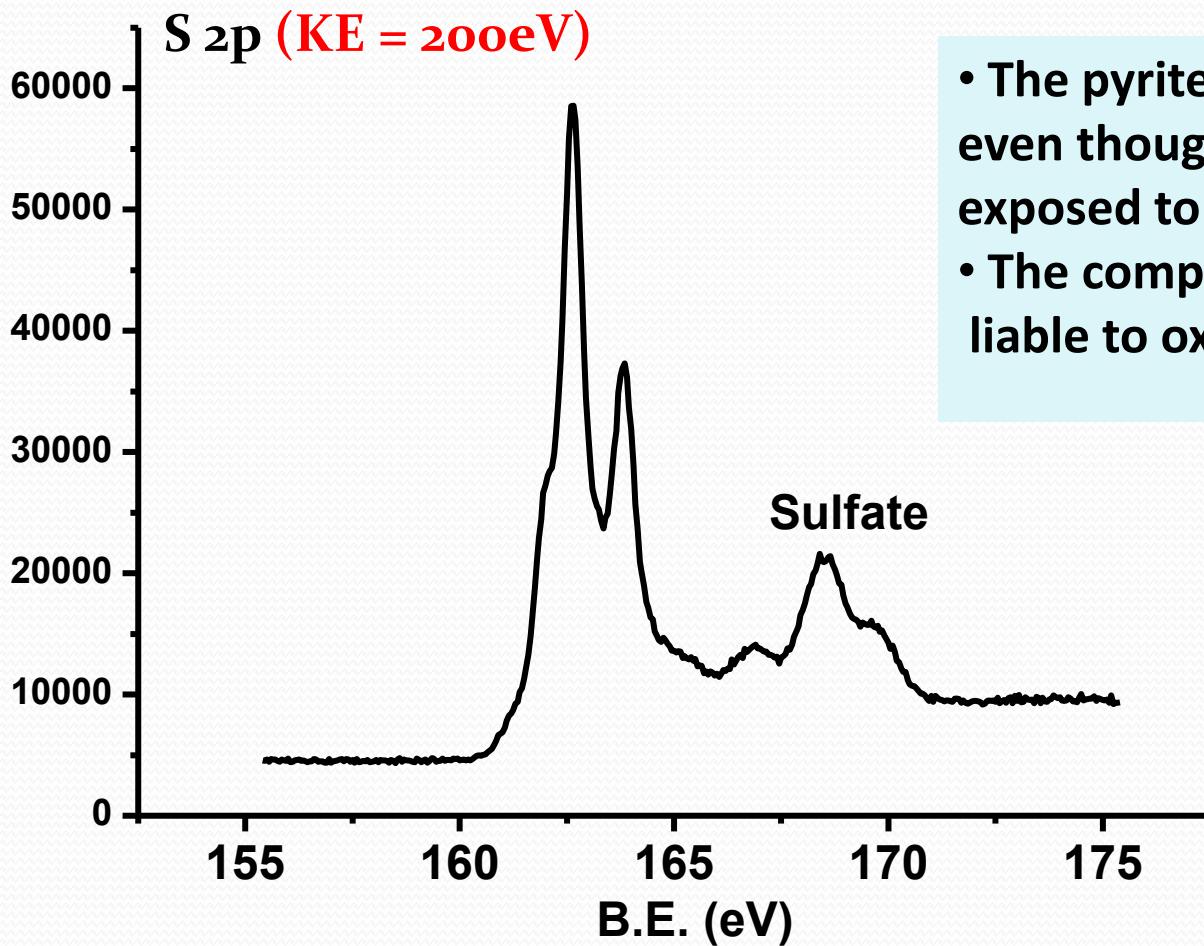
# Acid etched pyrite thin films on Si (in Berkeley)



# Acid etched pyrite thin films on Si (in Berkeley)

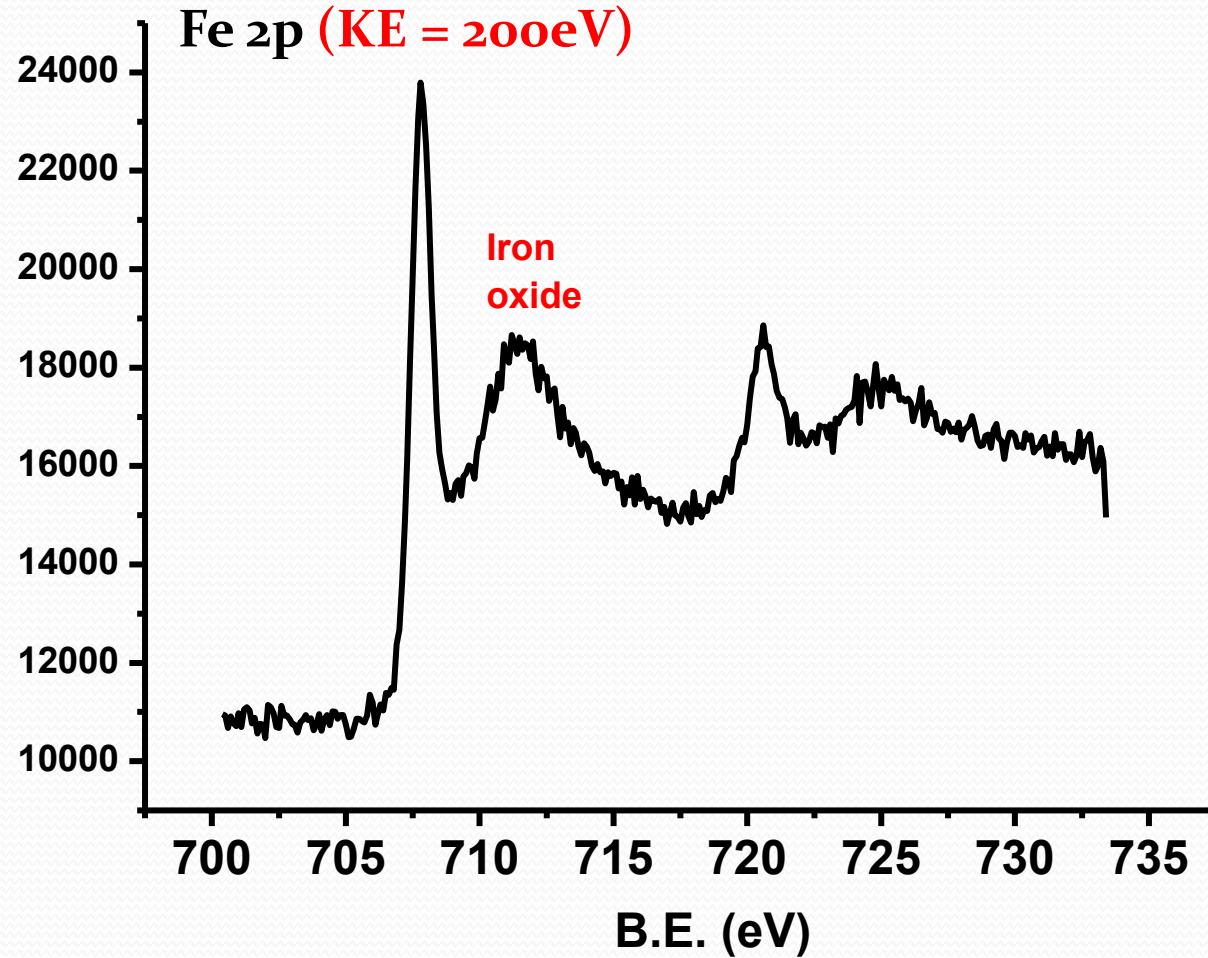


# Acid-etched pyrite thin films on Si after exposing to air 4 hours (in Berkeley)

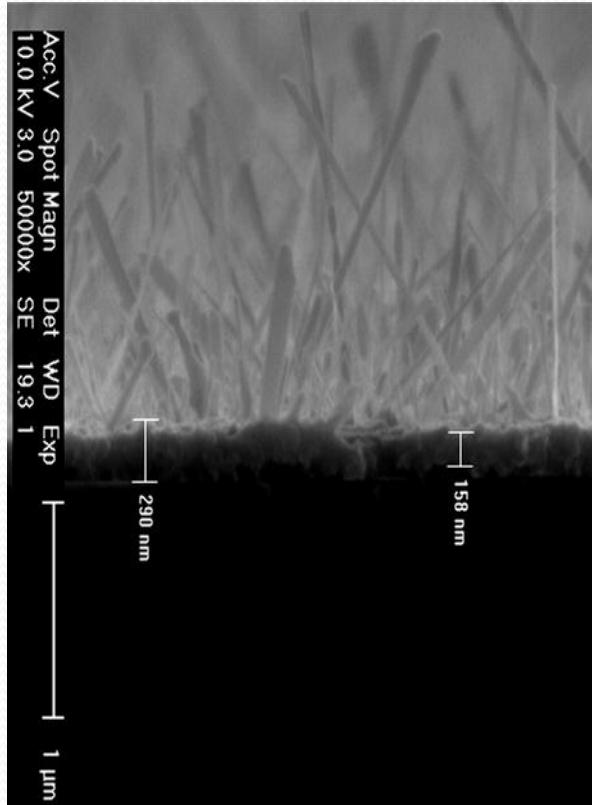


- The pyrite has been **oxidized** even though it only has been exposed to air for **4 hours**.
- The component,  **$S^{-2}$** , is the most liable to oxidize.

# Acid-etched pyrite thin films on Si after exposing to air 4 hours (in Berkeley)

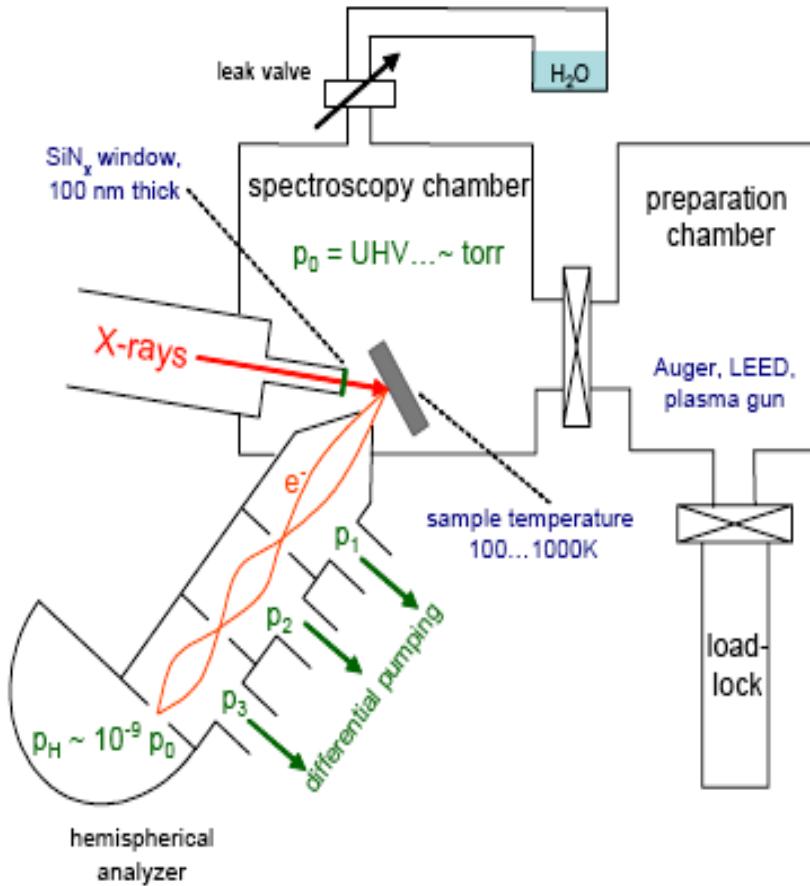


# Pyrite thin films on the Si substrate



The **pyrite nanowires** were formed on Si substrate instead of forming pyrite thin films.

# Setup of Ambient Pressure XPS



**Adjustable experimental conditions:**

- Adding H<sub>2</sub>O vapor up to **a few torr**.
- **Lower down** temperature ( $\sim 20$  degrees) for the sample (change humidity)
- **Rise up** temperature ( $\sim 1000$  degrees) for the sample.

# Conclusion

- Pyrite thin films on the glass
  - Na migrates to the surface of the pyrite thin films on the glass.
  - Ar sputtering is NOT a good way to remove the oxide layer due to sulfur preferential sputtering.
- Pyrite thin films on the quartz
  - The oxidation layers on the surface can be removed by the mixed acid but we still don't know when the oxide layer will be saturated.
- Pyrite thin films on the Si substrate
  - Using Synchrotron radiation, three sulfur surface chemical states can be revealed and the component, S<sup>-2</sup>, is the most liable to oxidize.

# Acknowledgements

- Prof. John Hemminger and the rest of our group.
- Beamline scientists in Lawrence Berkeley National Labs.
- Funding Sources

